NPN Epitaxial Silicon Transistor

KSC1815

Features

- Audio Frequency Amplifier and High-Frequency OSC
- Complement to KSA1015
- Collector-Base Voltage: V_{CBO} = 50 V
- This is a Pb-Free Device

MAXIMUM RATINGS (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Value	Unit
V _{CBO}	VCBO Collector-Base Voltage VCEO Collector-Emitter Voltage VEBO Emitter-Base Voltage		V
V _{CEO}			V
V _{EBO}			V
I _C	Collector Current	150	mA
Ι _Β	Base Current	50	mA
T _J Junction Temperature		150	°C
T _{STG} Storage Temperature Range		-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.) (Note 1)

Symbol	Parameter	Max.	Unit
P_{D}	Total Device Dissipation	400	mW
	Derate Above 25°C	3.2	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	312	°C/W

^{1.} PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.



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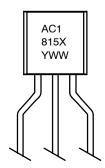
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- 1. Emitter
- 2. Collector
- 3. Base

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MARKING DIAGRAM



A = Assembly Code C1815 = Device Code X = O / Y / GR / L YWW = Date Code

ORDERING INFORMATION

Device	Package	Shipping
KSC1815YTA	TO-92 3L (Pb-Free)	2000 / Fan-Fold

KSC1815

ELECTRICAL CHARACTERISTICS (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV _{CBO}	Collector-Base Voltage	I _C = 1 mA, I _E = 0	60			V
BV _{CEO}	Collector-Emitter Voltage	I _C = 10 mA, I _B = 0	50			V
BV _{EBO}	Emitter-Base Voltage	$I_E = 10 \mu A, I_C = 0$	5			V
I _{CBO}	Collector Cut-Off Current	V _{CB} = 60 V, I _E = 0			0.1	μΑ
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 5 V, I _C = 0			0.1	μΑ
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 100 mA, I _B = 10 mA		0.10	0.25	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 100 mA, I _B = 10 mA			1.0	V
h _{FE1}	DC Current Gain	$V_{CE} = 6 \text{ V}, I_{C} = 2 \text{ mA}$	70		700	
h _{FE2}		V _{CE} = 6 V, I _C = 150 mA	25			
f _T	Current Gain Bandwidth Product	V _{CE} = 10 V, I _C = 1 mA	80			MHz
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz		2.0	3.0	pF
NF	Noise Figure	V_{CE} = 6 V, I_{C} = 0.1 mA, R _S = 10 k Ω , f = 1 kHz		1.0	10.0	dB

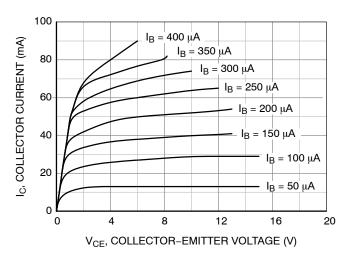
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

h_{FE} CLASSIFICATION

Classification	0	Υ	GR	L
H _{FE1}	70 ~ 140	120 ~ 240	200 ~ 400	350 ~ 700

KSC1815

TYPICAL PERFORMANCE CHARACTERISTICS



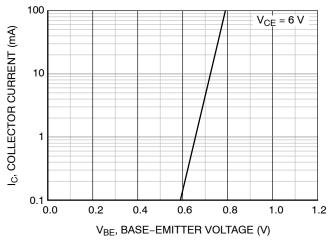
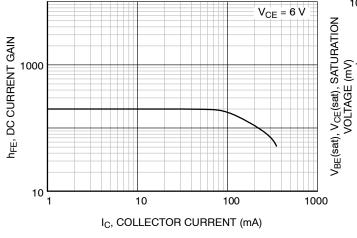


Figure 1. Static Characteristic

Figure 2. Static Characteristic



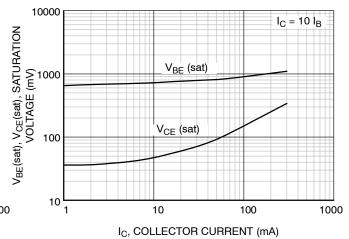
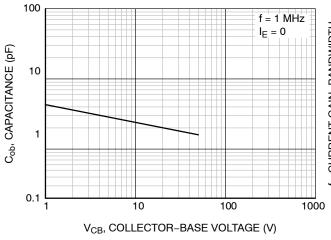


Figure 3. DC Current Gain

Figure 4. Base–Emitter Saturation Voltage and Collector–Emitter Saturation Voltage



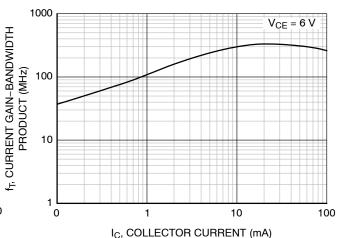


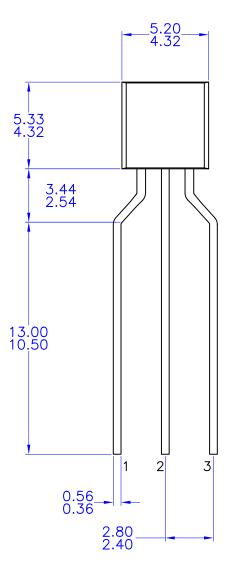
Figure 5. Output Capacitance

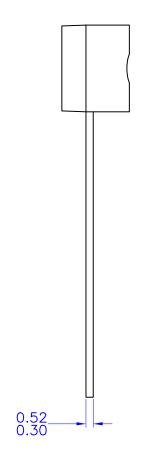
Figure 6. Current Gain Bandwidth Product

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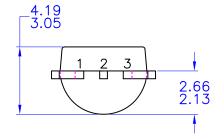
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NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994



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